

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_A = +25^\circ C$
100V	16m Ω @ $V_{GS} = 10V$	8.3A
	18m Ω @ $V_{GS} = 6V$	7.9A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

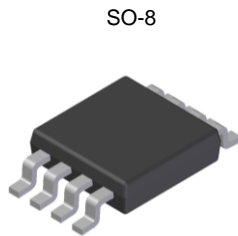
Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

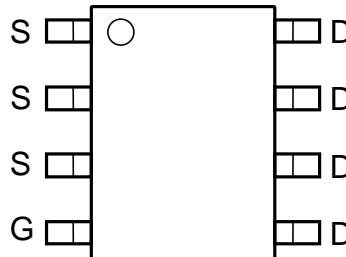
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

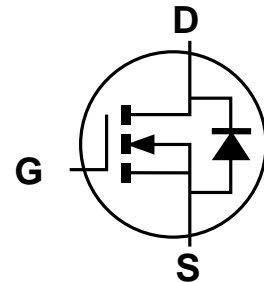
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.074 grams (Approximate)



Top View



Top View
Internal Schematic



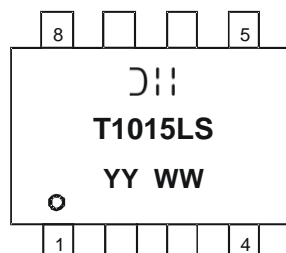
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H015LSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- ⌋|| = Manufacturer's Marking
 T1015LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or \overline{YY} = Year (ex: 16 = 2016)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	Steady State T _A = +25°C T _A = +70°C	8.3 6.7	A
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	54	A	
Avalanche Current (Note 8) L = 3mH	I _{AS}	7.5	A	
Avalanche Energy (Note 8) L = 3mH	E _{AS}	85	mJ	

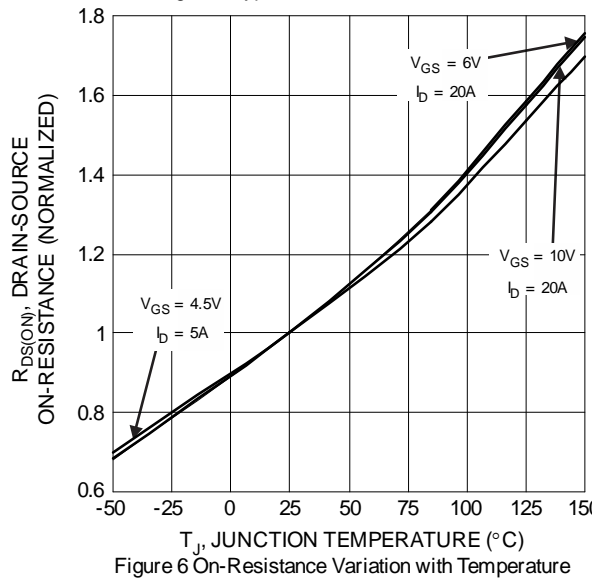
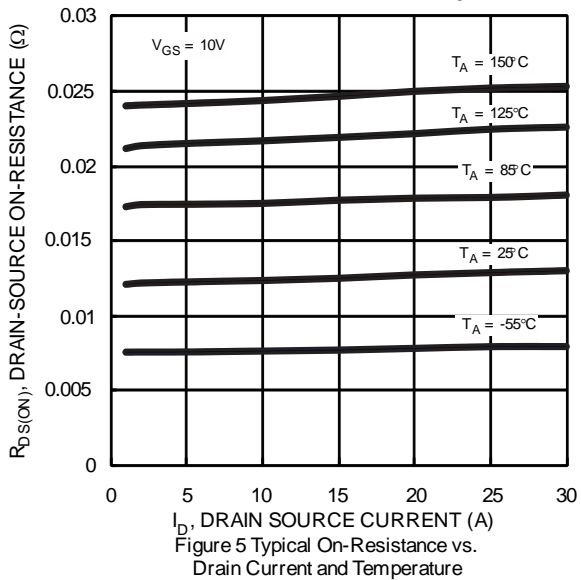
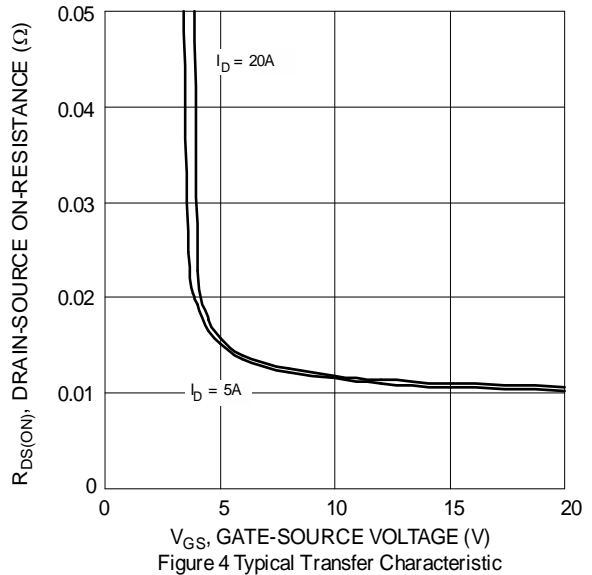
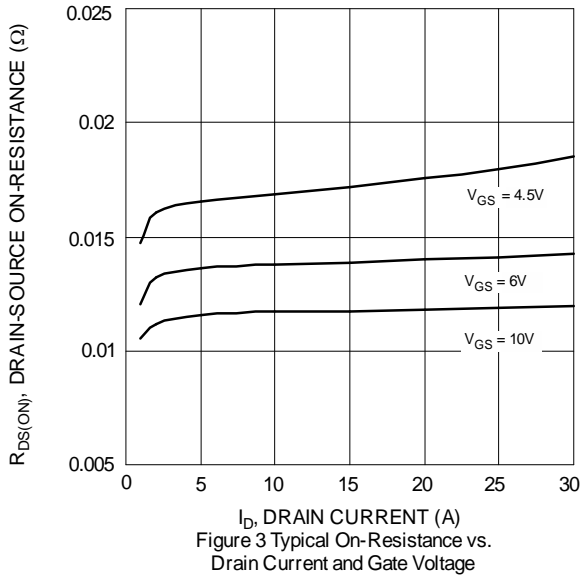
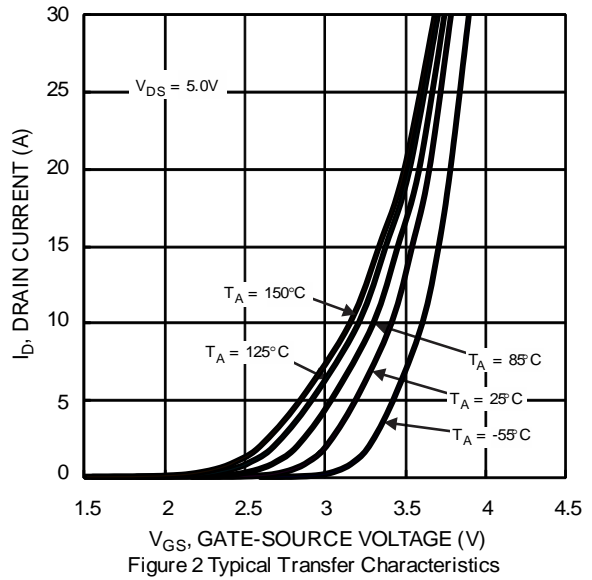
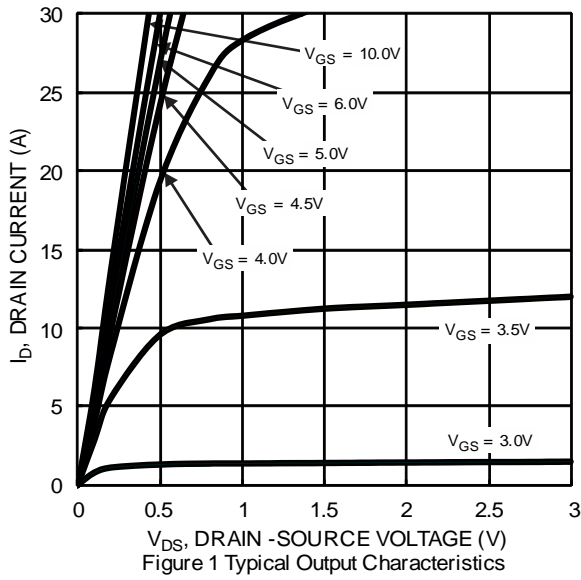
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	100	°C/W
Total Power Dissipation (Note 6)	P _D	1.67	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	75	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	12	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.4	2.3	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12	16	mΩ	V _{GS} = 10V, I _D = 20A
		—	14.5	18		V _{GS} = 6V, I _D = 20A
		—	17	25		V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.9	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1,871	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	261	—		
Reverse Transfer Capacitance	C _{RSS}	—	7	—		
Gate Resistance	R _G	—	0.75	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	33.3	—	nC	V _{DD} = 50V, I _D = 10A, V _{GS} = 10V
Gate-Source Charge	Q _{GS}	—	6.9	—		
Gate-Drain Charge	Q _{GD}	—	5.1	—		
Turn-On Delay Time	t _{D(ON)}	—	6.5	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 10A, R _G = 6Ω
Turn-On Rise Time	t _R	—	7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	19.7	—		
Turn-Off Fall Time	t _F	—	8.1	—		
Reverse Recovery Time	t _{RR}	—	37.9	—	ns	I _F = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	51.9	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.



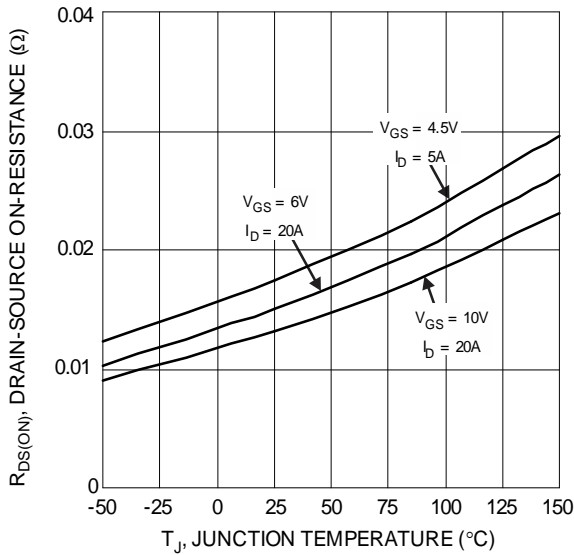


Figure 7 On-Resistance Variation with Junction Temperature

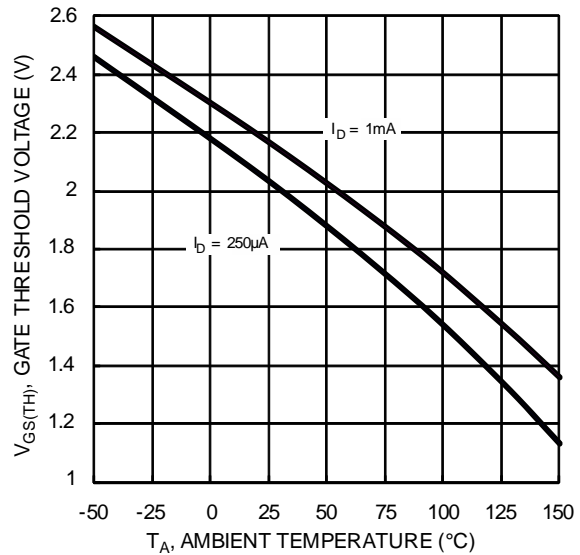


Figure 8 Gate Threshold Variation vs. Ambient Temperature

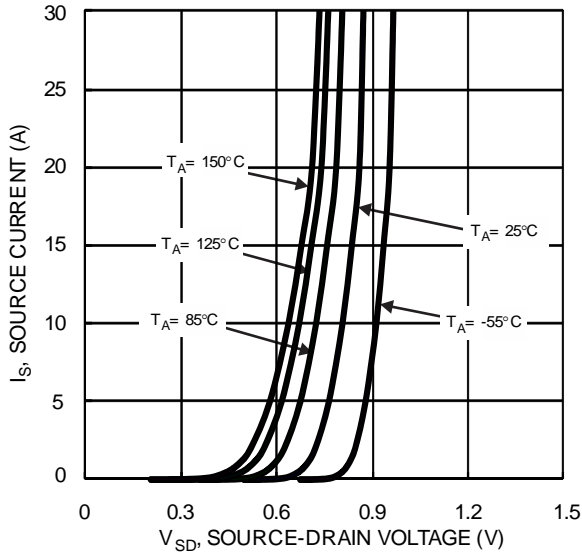


Figure 9 Diode Forward Voltage vs. Current

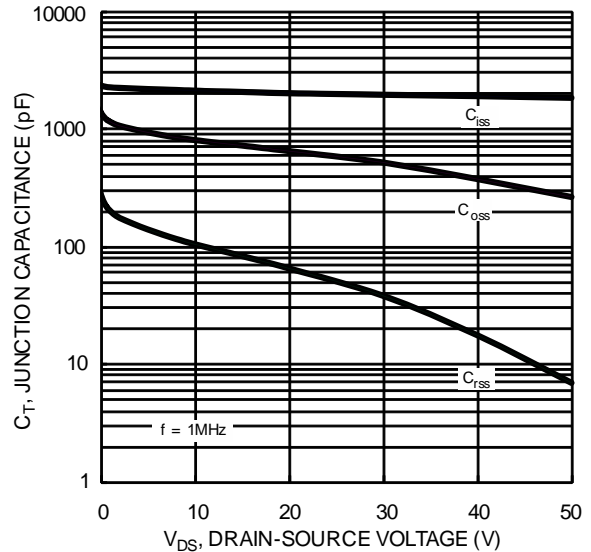


Figure 10 Typical Junction Capacitance

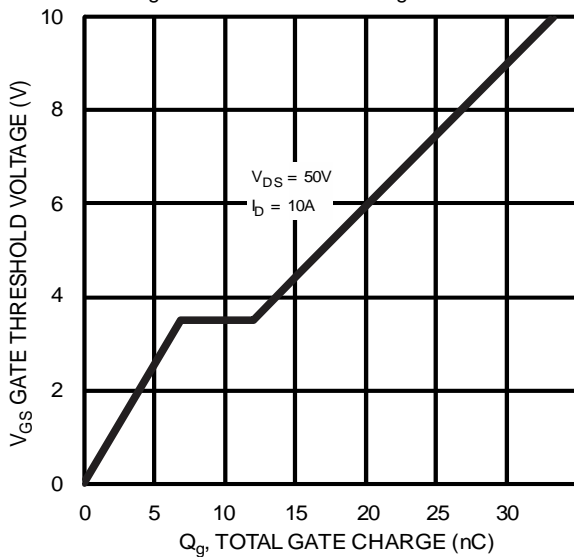


Figure 11 Gate Charge

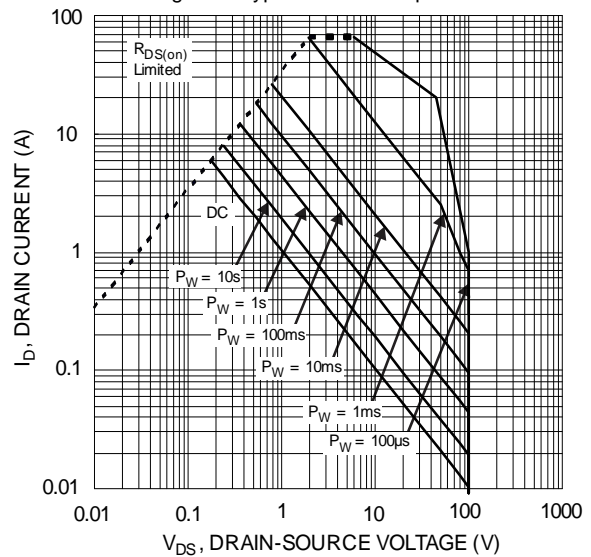
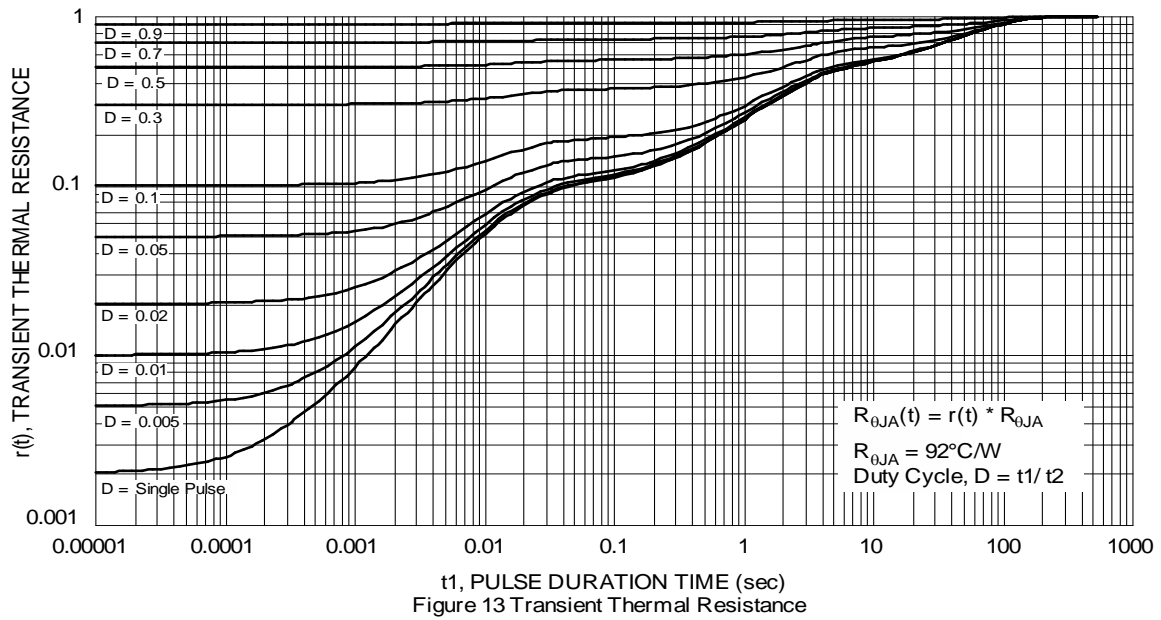


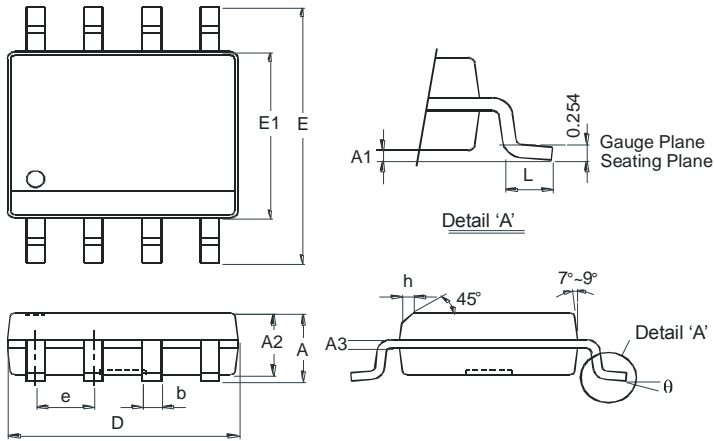
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

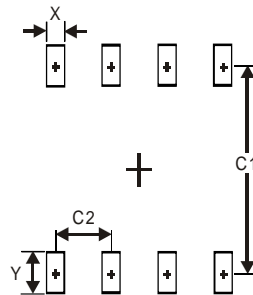


SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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